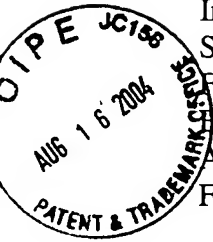


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re Application of: D'Evelyn, et al.
 Serial Number: 10/699,504
 Filed: 10/31/2003
 Examiner: To be assigned
 Art Unit: 1765
 For: HIGH PRESSURE/HIGH TEMPERATURE APPARATUS WITH IMPROVED
 TEMPERATURE CONTROL FOR CRYSTAL GROWTH

Mail Stop Non-Fee Amendment
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of the Search Report in a corresponding foreign patent application, a copy of the cited references and Form PTO-1449. Please make these of record in the above-referenced application.

There references are relevant because they were cited during the prosecution of a counterpart foreign application.

If any fee is required, this is a request therefore for the Commissioner to charge Deposit Account No. 50-2339 (General Electric Company)

GE Advanced Materials
 One Plastics Avenue
 Pittsfield, MA 01201
 August 12, 2004

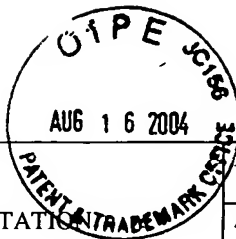
Hanh T. Pham
 Attorney of Record
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 Telephone No.: (413) 448-4664

CERTIFICATE OF MAILING (37 CFR 1.8a)

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Postal Service on the date shown below with sufficient postage as First Class mail in an envelope addressed to the: Commissioner of Patents and Trademarks, Alexandria, VA 22313-1450, Mail Stop Non-Fee Amendment.

Date: August 12, 2004

Judith A. Rowe

Form PTO-1449
(Reproduced)INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
(Use several sheets if necessary)Docket Number (Optional)
130894-2Application Number
10/699504Applicant
GENERAL ELECTRIC COMPANYFiling Date
10/31/2003Group Art Unit
1765

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	US2003/140845	07/31/03	D'Evelyn et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	NO
	EP0220462	05/06/87	Europe				
	EP0157393	10/09/85	Europe				
	GB922619	04/03/63	Great Britain				
	FR 1306951	10/19/62	France				
	WO 01/36080	05/25/01	World				
	EP0152726	08/28/85	Europe				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Hanser A D, et al: "Growth, doping and characterization of epitaxial thin films and patterned structures of AlN, GaN, and Al _x Ga _{1-x} N"; XP004364890
	Lawniczak-Jablonska K. et al.: "Polarization dependent x-ray absorption studies of the chemical bonds anisotropy in wurtzite GaN grown at different conditions"; XP004304294

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.